

**EAST - [thinsearch15.wsp:1]**

**File View Edit Tools Window Help**

**BRS: ferromagnetic and offset**

**BRS: 1 2**

**BRS:**

**BRS:**

**BRS: upside**

**Pending**

**Active**

**L2: (64) nitride adj memory**

**L1: (382) NROM**

**L3: (285) 1 and nitride**

**L4: (47278) bit adj line**

**L5: (175) 3 and 4**

**Failed**

**(0) AND adj logic**

**DBs: USPTO; US PGRIB; EPO; JPO; DERWENT; IBM, TDB**

**Detail option: OR**

**3 and 4**

**BRS home** **ISSN home** **Image** **Text** **HTML**

<b>U</b>	<b>I</b>	<b>Document ID</b>	<b>Issue Date</b>	<b>Pages</b>	<b>Title</b>	<b>Current OR</b>	<b>Current XRef</b>	<b>Retrieval Clu</b>	<b>Inventor</b>	<b>S</b>	<b>C</b>	<b>P</b>	<b>Image</b>	<b>Link</b>	
1	<input checked="" type="checkbox"/>	US 20030185071	20031002	24	Nonvolatile semiconductor memory device and method of manufacturing	365/200			Yoshino, Akira	<input checked="" type="checkbox"/>	US 2003				
2	<input checked="" type="checkbox"/>	US 20030185053	20031002	16	Fast program to program verify	365/185.18			Ogura, Seiki et al.	<input checked="" type="checkbox"/>	US 2003				
3	<input checked="" type="checkbox"/>	US 20030174570	20030918	43	Semiconductor memory device having potential control circuit	365/230.03			Ooishi, Tsukasa	<input checked="" type="checkbox"/>	US 2003				
4	<input checked="" type="checkbox"/>	US 20030161183	20030828	120	Digital multilevel non-volatile memory system	365/185.03	365/185.2		Tran, Hieu Van	<input checked="" type="checkbox"/>	US 2003				
5	<input checked="" type="checkbox"/>	US 20030157758	20030821	73	Non-volatile semiconductor memory device and manufacturing method the	438/199			Ohtani, Jun et al.	<input checked="" type="checkbox"/>	US 2003				
6	<input checked="" type="checkbox"/>	US 20030155607	20030821	87	SEMICONDUCTOR INTEGRATED CIRCUIT	257/324			Kamigaki, Yoshiaki et al.	<input checked="" type="checkbox"/>	US 2003				
7	<input checked="" type="checkbox"/>	US 20030151946	20030814	46	Nonvolatile semiconductor memory device having control circuit	365/185.03			Ooishi, Tsukasa	<input checked="" type="checkbox"/>	US 2003				
8	<input checked="" type="checkbox"/>	US 20030145176	20030731	28	Mass storage device architecture and operation	711/154	711/104; 711/162		Dvir, Ran et al.	<input checked="" type="checkbox"/>	US 2003				
9	<input checked="" type="checkbox"/>	US 20030142544	20030731	24	Mass storage array and methods for operation thereof	365/185.16			Mazayn, Eduardo et al.	<input checked="" type="checkbox"/>	US 2003				
10	<input checked="" type="checkbox"/>	US 20030141532	20030731	23	Non-volatile semiconductor memory device of which bit line withstand volt	257/304			Kato, Hiroshi	<input checked="" type="checkbox"/>	US 2003				
11	<input checked="" type="checkbox"/>	US 20030134478	20030717	10	Non-volatile memory and fabrication thereof	438/275	438/278; 438/291		Lai, Han-Chao et al.	<input checked="" type="checkbox"/>	US 2003				
12	<input checked="" type="checkbox"/>	US 20030134476	20030717	9	Oxide-nitride-oxide structure	438/261			Rozin, Yakov et al.	<input checked="" type="checkbox"/>	US 2003				
13	<input checked="" type="checkbox"/>	US 20030132488	20030717	10	Non-volatile memory and fabrication thereof	257/390	257/391		Lai, Han-Chao et al.	<input checked="" type="checkbox"/>	US 2003				
14	<input checked="" type="checkbox"/>	US 20030128588	20030710	16	Fast program to program verify	365/185.18	365/185.21; 365/189.07		Ogura, Seiki et al.	<input checked="" type="checkbox"/>	US 2003				
15	<input checked="" type="checkbox"/>	US 20030123308	20030703		Fast program to program verify	365/200			Ogura, Seiki et al.	<input checked="" type="checkbox"/>					
16	<input checked="" type="checkbox"/>	US 20030123293	20030703		Fast program to program verify	365/185.18			Ogura, Seiki et al.	<input checked="" type="checkbox"/>					
17	<input checked="" type="checkbox"/>	US 20030123292	20030703		Fast program to program verify	365/185.18			Ogura, Seiki et al.	<input checked="" type="checkbox"/>					

**Details** **HTML**

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